

L Number	Hits	Search Text	DB	Time stamp
1	2340	257/296	USPAT	2002/12/24 09:39
2	355	257/311	USPAT	2002/12/24 09:39
3	384	257/318	USPAT	2002/12/24 09:39
4	433	257/320	USPAT	2002/12/24 09:39
5	986	257/314	USPAT	2002/12/24 09:39
6	1722	257/315	USPAT	2002/12/24 09:40
7	2065	257/316	USPAT	2002/12/24 09:40
8	456	257/319	USPAT	2002/12/24 09:40
9	1077	257/336	USPAT	2002/12/24 09:40
10	1256	257/344	USPAT	2002/12/24 09:40
11	108	257/549	USPAT	2002/12/24 09:40
12	87	257/550	USPAT	2002/12/24 09:40
-	0	(semiconductor adj device adj having adj2 flash adj memory adj cell) and non-volatile and floating and control and gate and spacer and shape and charge and storage	USPAT	2002/12/23 13:35
-	0	semiconductor adj device adj having adj2 flash adj memory adj cell	USPAT	2002/12/23 13:35
-	35	semiconductor and memory and cell and non-volatile and floating and control and gate and spacer and shape and charge and storage and device and electrode and sidewall	USPAT	2002/12/23 13:38
-	33	semiconductor and memory and cell and non-volatile and floating and control and gate and spacer and shape and charge and storage and device and electrode and sidewall and mask and conductive and region	USPAT	2002/12/23 13:38
-	0	(semiconductor and memory and cell and non-volatile and floating and control and gate and spacer and shape and charge and storage and device and electrode and sidewall and mask and conductive and region) and (charge adj storage adj region) and (gate adj mask)	USPAT	2002/12/23 13:39
-	0	(flash adj memory) and (charge adj storage adj region) and (gate adj mask) and cell	USPAT	2002/12/23 13:40
-	33	(semiconductor and memory and cell and non-volatile and floating and control and gate and spacer and shape and charge and storage and device and electrode and sidewall and mask and conductive and region) and (first or unit or symmetrical or opposite or storage or region or side or wall or spacer or adjacent or mask or photo or resist or LDD or halo or highly or doped or drain or source)	USPAT	2002/12/23 14:24
-	1	("5930631").PN.	USPAT	2002/12/23 14:00
-	1	("5280446").PN.	USPAT	2002/12/23 14:01
-	1	("5455792").PN.	USPAT	2002/12/23 14:01
-	1	("4698787").PN.	USPAT	2002/12/23 14:02
-	1	("4558344").PN.	USPAT	2002/12/23 14:02
-	1	("4783766").PN.	USPAT	2002/12/23 14:02
-	1	("4794565").PN.	USPAT	2002/12/23 14:03
-	1	(("4794565").PN.) and (first or unit or symmetrical or opposite or storage or region or side or wall or spacer or adjacent or mask or photo or resist or LDD or halo or highly or doped or drain or source)	USPAT	2002/12/23 14:15
-	67	gate and control and floating and ONO and spacer and memory and cell and flash and non-volatile and source and drain and LDD	USPAT	2002/12/23 14:17
-	5	(gate and control and floating and ONO and spacer and memory and cell and flash and non-volatile and source and drain and LDD) and (gate adj mask) and storage	USPAT	2002/12/23 14:18
-	67	(gate and control and floating and ONO and spacer and memory and cell and flash and non-volatile and source and drain and LDD) and (first or unit or symmetrical or opposite or storage or region or side or wall or spacer or adjacent or mask or photo or resist or LDD or halo or highly or doped or drain or source)	USPAT	2002/12/24 09:38

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